

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

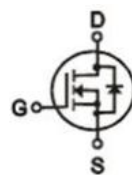
• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Oring switches
- Power Tools

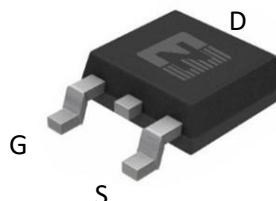
• Product Summary



$$V_{DS}=60V$$

$$R_{DS(ON)}=9m\Omega$$

$$I_D=50A$$



TO-252

• Ordering Information:

Part NO.	ZMS090N06D
Marking	ZMS090N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	50	A
	$I_{D@TC=75^\circ C}$	38	A
	$I_{D@TC=100^\circ C}$	31.5	A
Pulsed Drain Current ^①	I_{DM}	150	A
Total Power Dissipation	$P_{D@TC=25^\circ C}$	54	W
Total Power Dissipation	$P_{D@TA=25^\circ C}$	2	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	47	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.3	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	63	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10A$		9	11	m Ω
		$V_{GS}=4.5V, I_D=5A$		12	14	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$		14		S
Source-drain voltage	V_{SD}	$I_S=10A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R_g	$f = 1MHz$		1.5		Ω
Input capacitance	C_{iss}	$f = 1MHz$ $V_{DS}=25V$	-	960	-	pF
Output capacitance	C_{oss}		-	460	-	
Reverse transfer capacitance	C_{rss}		-	35	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	14	-	nC
Gate - Source charge	Q_{gs}	$I_D = 8A$	-	2.8	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	2.2	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

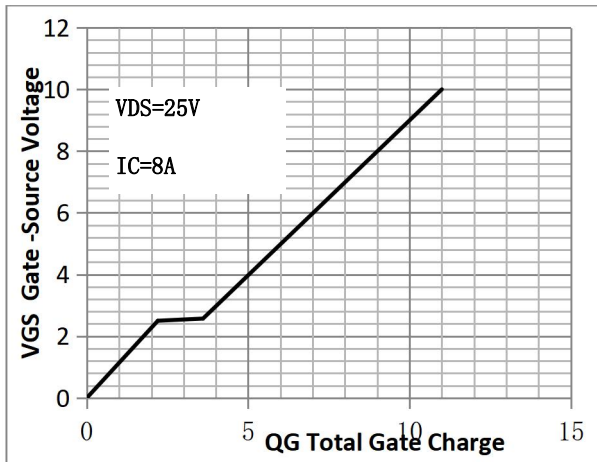


Fig.2 Capacitance Characteristics

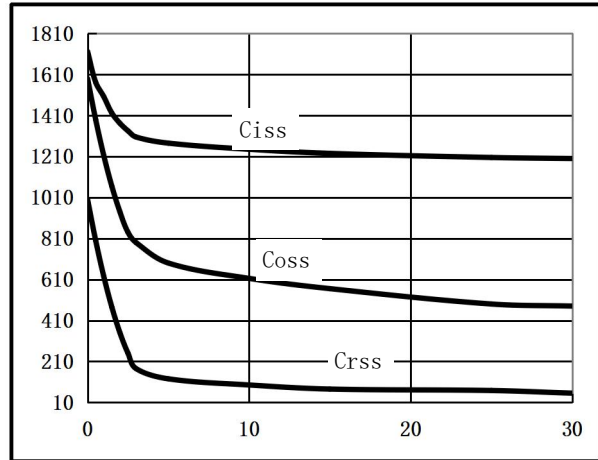


Fig.3 Power Dissipation

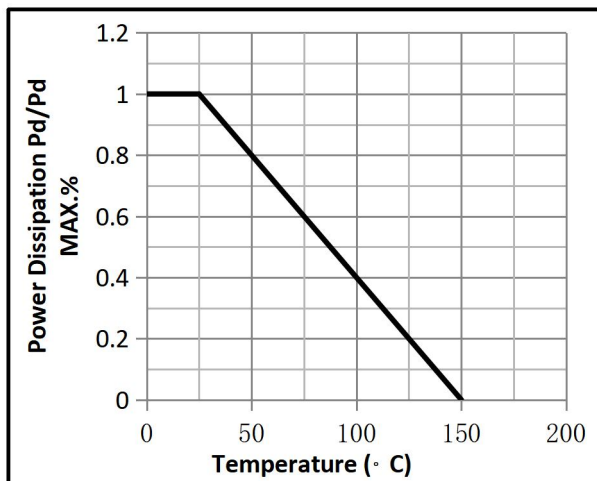


Fig.4 Typical output Characteristics

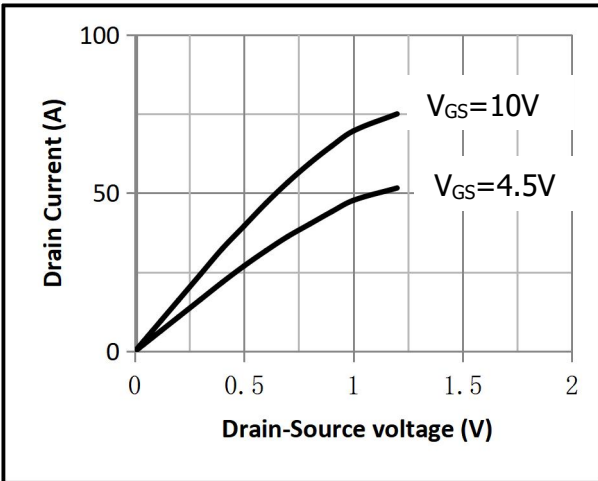


Fig.5 Threshold Voltage V.S Junction Temperature

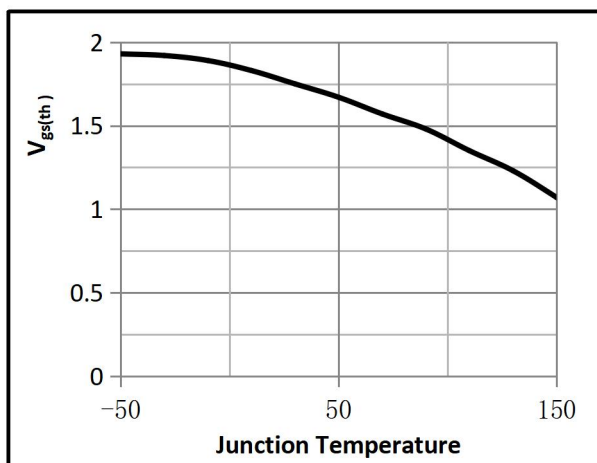


Fig.6 Resistance V.S Drain Current

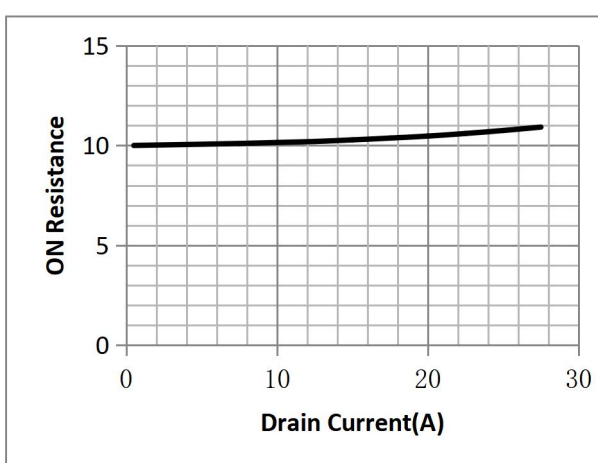


Fig.7 On-Resistance VS Gate Source Voltage

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Fig.8 On-Resistance V.S Junction Temperature

3 <http://www.zmjssemi.com>

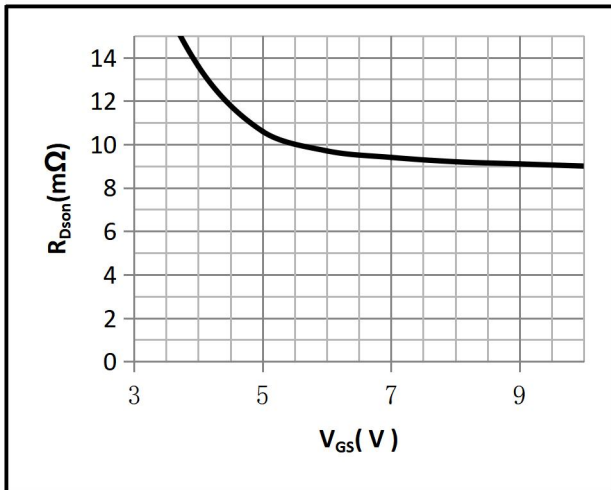


Fig.9 Switching Time Measurement Circuit

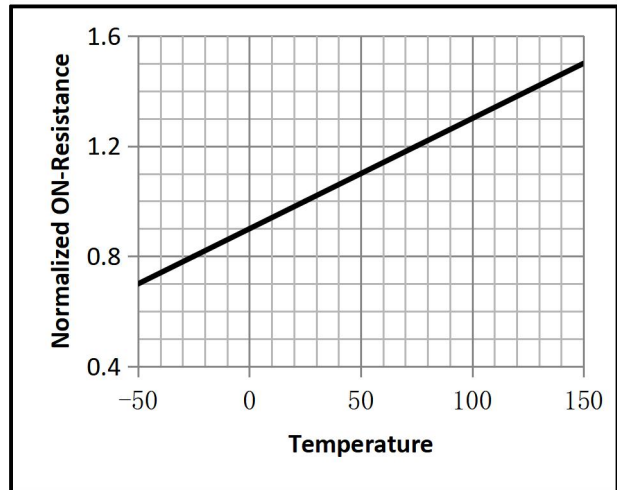


Fig.10 Gate Charge Waveform

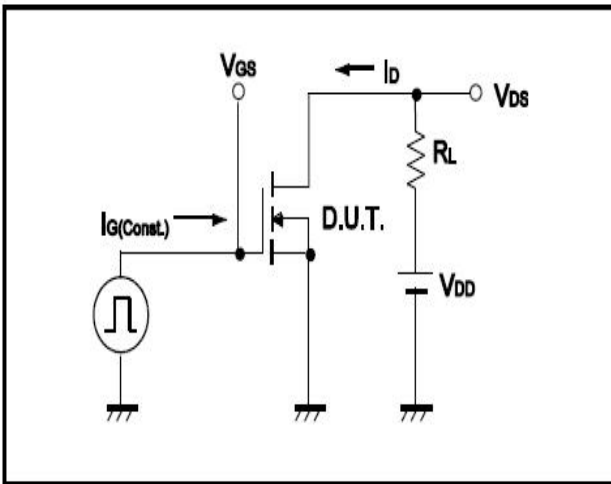


Fig.11 Switching Time Measurement Circuit

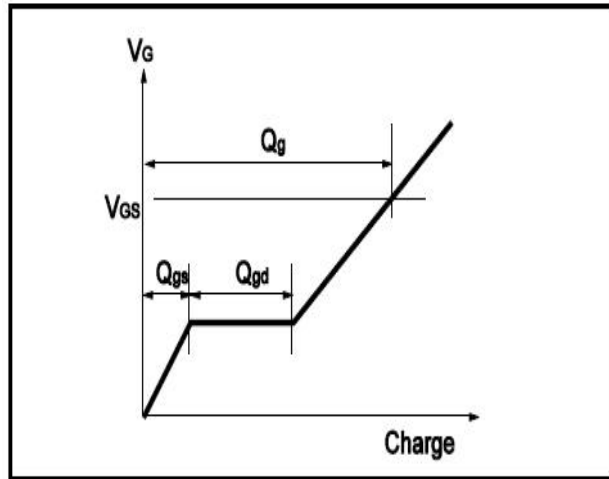
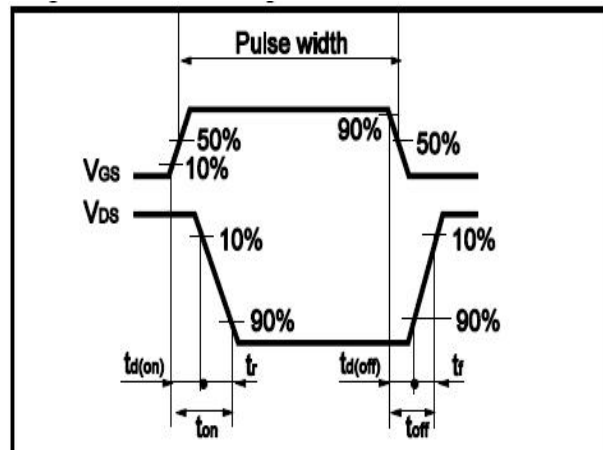
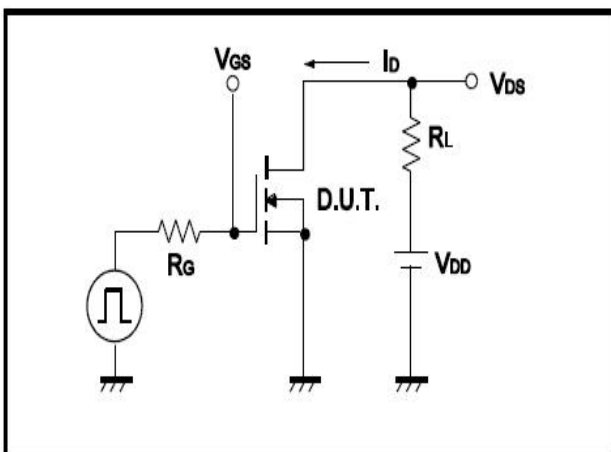


Fig.12 Gate Charge Waveform



•Dimensions(TO-252)

Unit: mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

